

전자물리특강-OLED

White OLEDs for displays and lighting

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Brief history of Lighting

- 500,000 years ago – fire, 1st torch
- 70,000 years ago – 1st lamp (wick)
- 1,000 BC – 1st candle
- 1772 gas lighting
- 1879 T. A. Edison, incandescent filament lamp: Dawn of electric lighting.
- 1907 H. J. Round, 1st LED (SiC), Electrical World 49, 309 (1907)
- 1910 P. Claude, discharge lamps filled with inert gases
- 1938 GE and Westinghouse Electric Co. white fluorescent lamps.
- 1962 N. Holonyak Jr. and Bevaqua, GaAsP (visible light – red)
- 1987 C. W. Tang, OLED (Alq₃, Green)
- 1995 S. Nakamura et al, GaInN LED (blue & Green)

pyroluminescence

History of Lighting
(<http://lighting.sandia.gov/>)



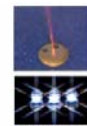
Fire



Candles and Lamps



Bulbs and Tubes



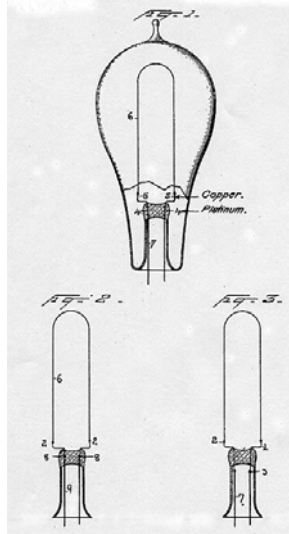
Semiconductors

→ More Efficient, Convenient

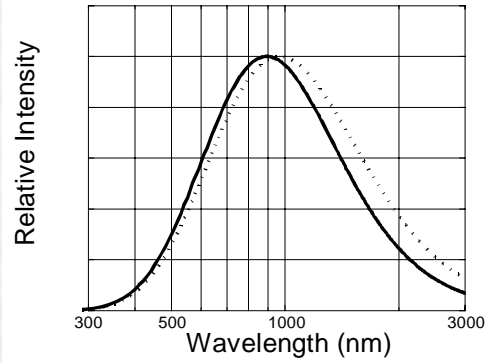


Incandescent Lamp

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black body (dot) and tungsten radiator (solid line) at 3000 K



Edison's US. Patent No.
444,530 (issued Jan 13, 1891)

Now, Lifetime ~ 2000 h
Efficiency ~ 17 lm/W



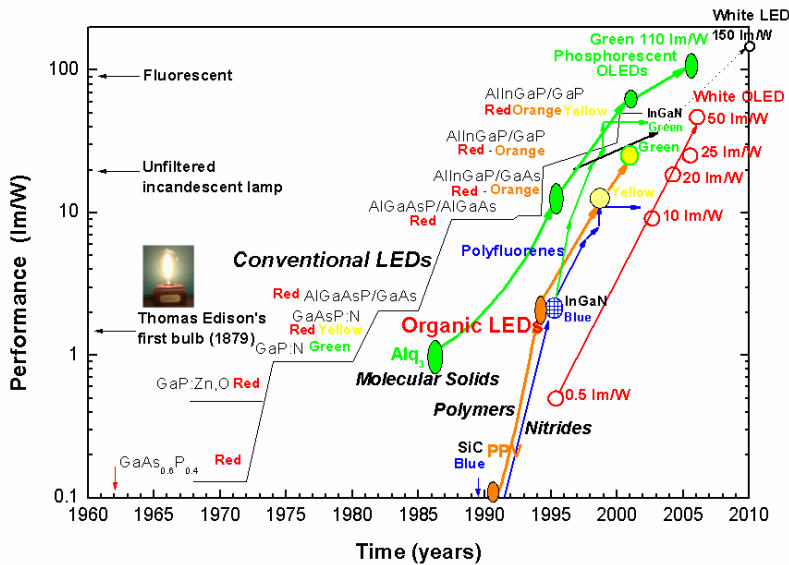
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Evolution of OLED Performance

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Updated the data in J. R. Sheats *et al.*, Science **273**, 884 (1996).



SEC
40" WXGA
a-Si AMOLED

Mass production of
AMOLED
Samsung SDI



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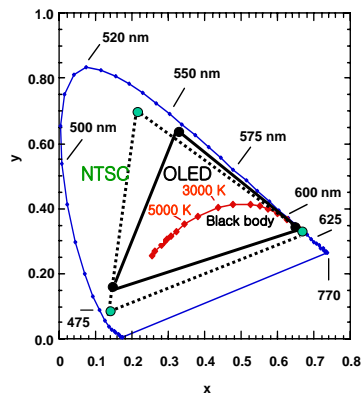
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Performance of RGB OLED Devices

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		Color	CIE (x,y)	Efficiency (cd/A)	Half-Life (hr)
저분자	외관	Red	0.65, 0.35	5.5	>80,000 @ 1000 cd/m ²
		Green	0.32, 0.62	19	40,000 @ 1000 cd/m ²
		Light blue	0.17, 0.30	12	21,000 @ 1000 cd/m ²
		Blue	0.15, 0.15	5.9	7,000 @ 1000 cd/m ²
		White	0.30, 0.34	12	23,000 @ 1000 cd/m ²
	인관	Red	0.65, 0.35	15	>22,000 @ 500 cd/m ²
		Orange	0.61, 0.38	22	15,000 @ 300 cd/m ²
		Green	0.31, 0.64	27	25,000 @ 600 cd/m ²
		Light blue	0.14, 0.23	8	-
		White	0.39, 0.39	38	-
고분자	외관	Red	0.68, 0.32	1.7	1790 @ 1000 cd/m ²
		Orange	0.58, 0.42	0.9	8138 @ 1000 nit
		Yellow	0.50, 0.49	2.1	2420 @ 4000 cd/m ²
		Green	0.43, 0.55	7.7	2912 @ 2000 cd/m ²
		Blue	0.16, 0.22	6.9	>1147 @ 800 cd/m ²
		White	0.30, 0.33	3.8	235 @ 800 cd/m ²
	인관	Red	0.67, 0.28	1.3	>8350 @ 100 cd/m ²
		Green	0.36, 0.59	22.8	2649 @ 400 cd/m ²

OLED의 색 좌표

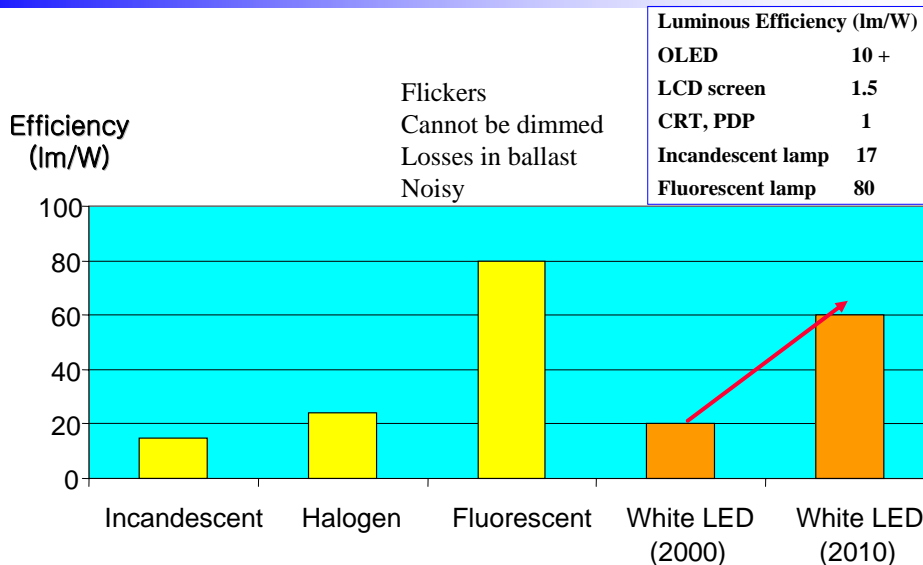


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Solid State Lighting

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Ref. A. Zukauskas, M. S. Shur, R. Caska, Introduction to Solid-State Lighting



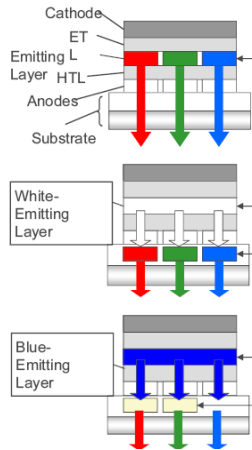
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White Organic Light-Emitting Devices

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- Full-Color Display
- Backlight of TFT-LCD
- Lighting – Light signs, decorative lighting, glowing wall paper, ceiling lights, etc.



I. Patterned-Emitting Layer	
Advantages	Disadvantages
<ul style="list-style-type: none"> ▪ High efficiency ▪ Good color 	<ul style="list-style-type: none"> • Aperture ratio issues • Typically uses shadow masking for RGB patterning • Differential aging of RGB
II. White-Emitting Layer with Color-Filter Array	
Advantages	Disadvantages
<ul style="list-style-type: none"> ▪ Unpatterned emitting layer (no masks) ▪ Aperture ratio not affected by RGB patterning ▪ Enabled by high-efficiency white 	<ul style="list-style-type: none"> • Loss of efficiency is due to filter absorption
III. Blue-Emitting Layer with Color-Change Medium	
Advantages	Disadvantages
<ul style="list-style-type: none"> ▪ Unpatterned emitting layer (no masks) 	<ul style="list-style-type: none"> • Requires high efficiency blue • Blue stability typically poorest • Compatibility of CCM materials



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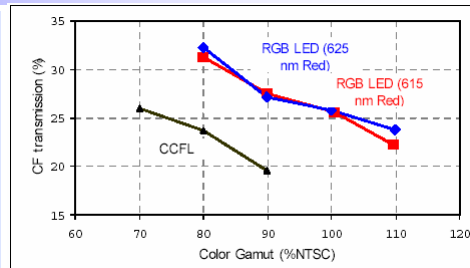
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LED backlighting

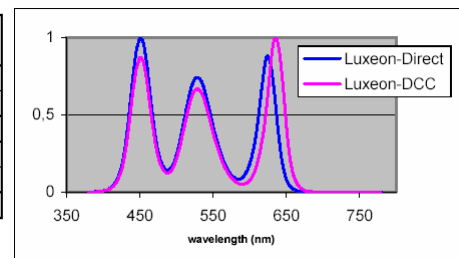
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Advantages of using LEDs over conventional light sources such as CCFL:

- long life
- ruggedness
- high frequency dynamical operation
- Hg-free light source
- Better color gamut



	Dominant Wavelength (nm)	Efficacy (Lm/W, 25°C)
Red in Luxeon-DCC	625	55
Red in Luxeon-Direct	617	60
Green	533	46
Blue	452	5.5
RGB-White	-	37
White (phosphor-converted)	-	35



Wiep Folkerts (Lumileds Lighting), SID 04 Digest, p. 1226



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- Improve efficiency of light generation
- Improve efficiency of light extraction
- Improve quality of light
- Reduce cost



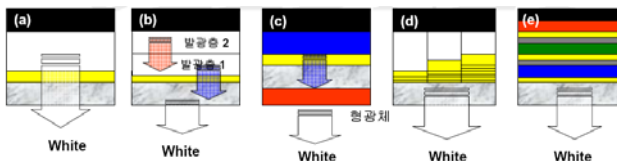
Methods of Making White LEDs

- Wavelength Conversion
 1. Blue LED with phosphors
 2. UV LED with several phosphors
- Color Mixing
 3. Two or more emitting layers of different colors.
 - white light with a high color rendering index (CRI).
 - relatively easy to change the hue for different applications.



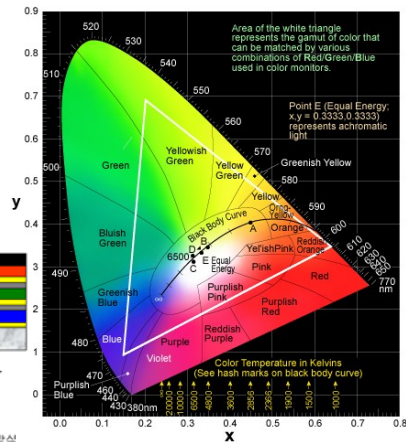
$$R + G + B = W$$

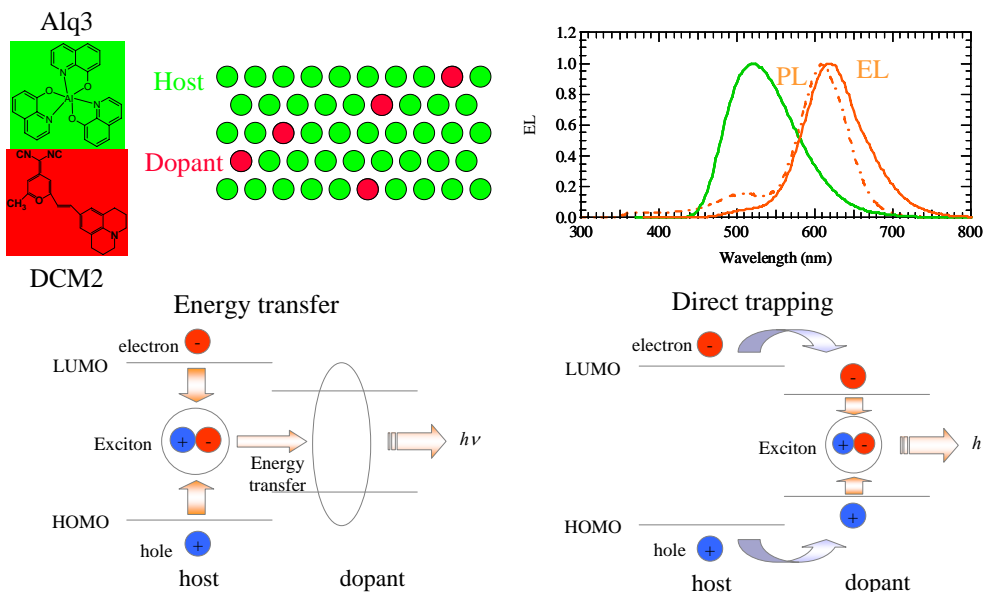
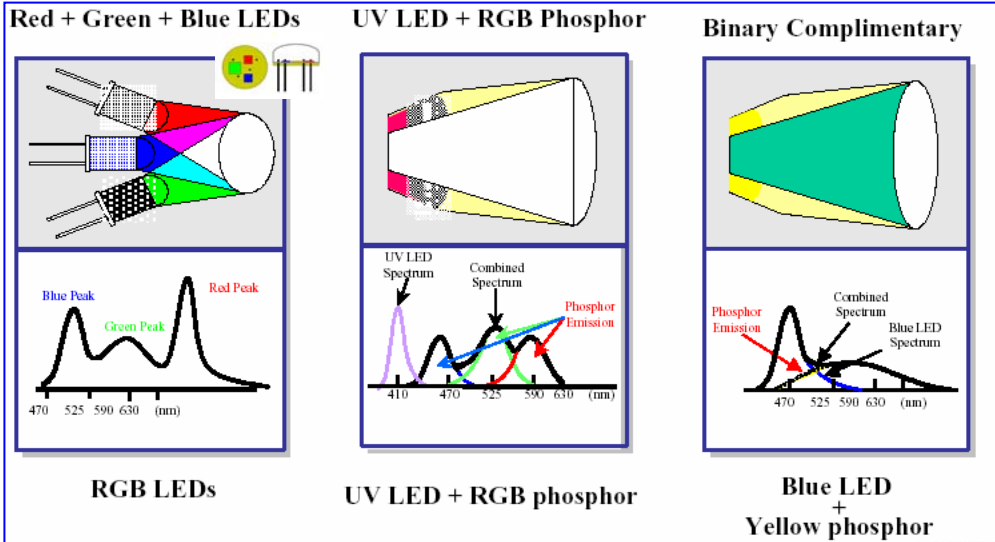
$$R + C = W \quad G + M = W \quad B + Y = W$$



OLED NET

그림 7. 백색 OLED 제조 방식: (a) 단일층 발광, (b) 이중층 발광, (c) 색변환 방식, (d) Microcavity 방식, (e) 소자적층 방식

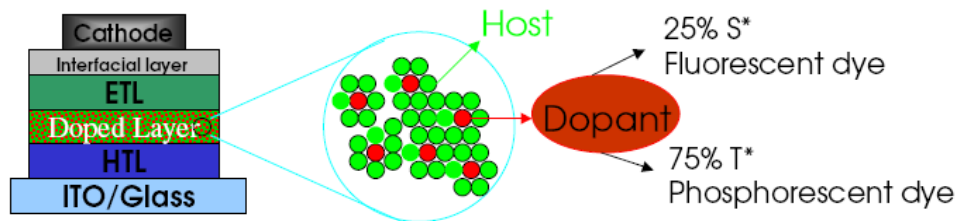




Doping in OLEDs

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- Doping fluorescent dyes
C. W. Tang, S. A. VanSlyke, and C. H. Chen, J. Appl. Phys. **65**, 3610 (1989)
- Doping phosphorescent dyes
M. A. Baldo, et al, Nature 395, 151 (1998)
- Effects of doping:
 1. Color tuning.
 2. Increase the device quantum efficiency
 3. In general, the doped layer is more thermally stable than the undoped layer (increase of entropy).
 4. Proper dopants can increase the operational lifetime of the device.



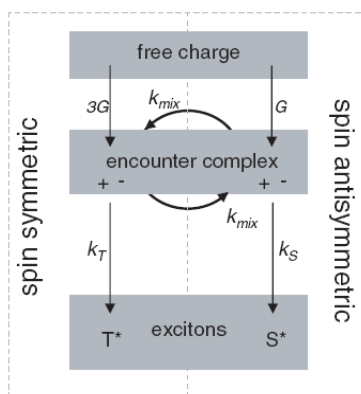
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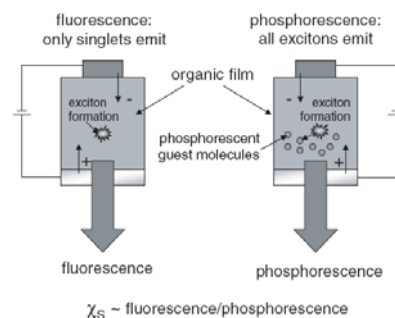
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Exciton formation

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$$\begin{aligned} \text{If } k_S > k_T, \quad \chi_S &> \frac{1}{4} \\ \text{If } k_S < k_T, \quad \chi_S &< \frac{1}{4} \\ \text{If } k_{mix} = 0, \quad \chi_S &= \frac{1}{4} \end{aligned}$$



Caution for this simple method:

- (1) It is necessary to correct for the differing photoluminescent efficiencies of the fluorescent and phosphorescent guest molecules.
- (2) The efficiency of energy transfer to both guest materials must be determined to ensure that radiative emission accurately reflects the number of excitons formed within the device.
- (3) The impact of quenching phenomena must be calculated for both singlet and triplet excitons.
- (4) When applied to polymeric systems, it is especially important to ensure that excitons are formed on the polymeric host and not on the small molecularweight phosphorescent guest.

M. Baldo and M. Segal, phys. stat. sol. (a) 201, 1205 (2004)



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Fluorescent Dye doping

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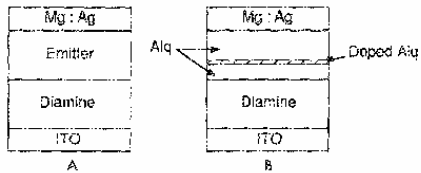


FIG. 1. Configurations of multilayer organic EL cells: (a) ITO/diamine/doped or undoped Alq/Mg:Ag. (b) ITO/diamine/Alq/doped Alq/Mg:Ag.

C. W. Tang and S. A. VanSlyke, C. H. Chen,
J. Appl. Phys. **65**, 3610 (1989)

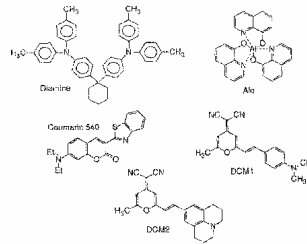


FIG. 2. Molecular structures of (1) diamine, (2) Alq, and (3) CS40, DCM1, and DCM2.

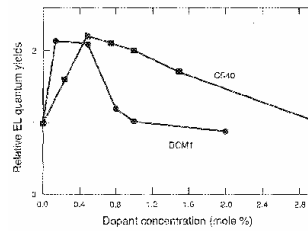
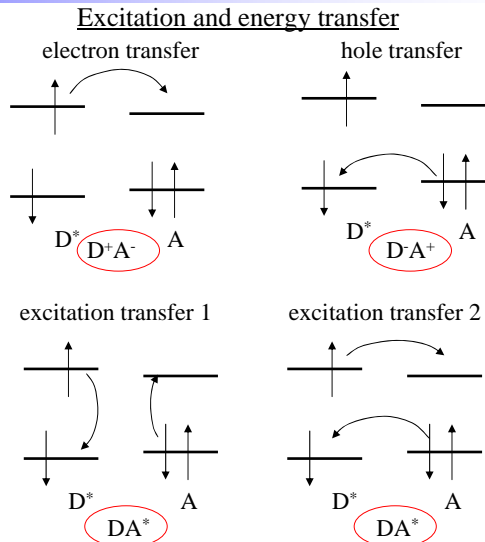
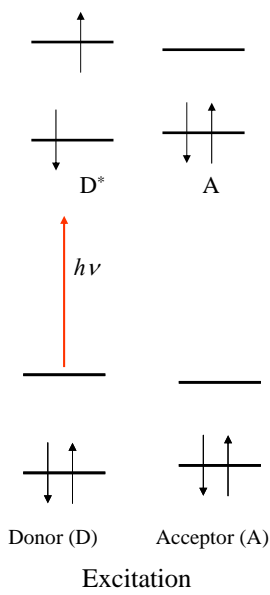


FIG. 10. Relative EL quantum efficiencies as a function of dopant concentration in Alq.



Excitonic interaction and excitation transfer

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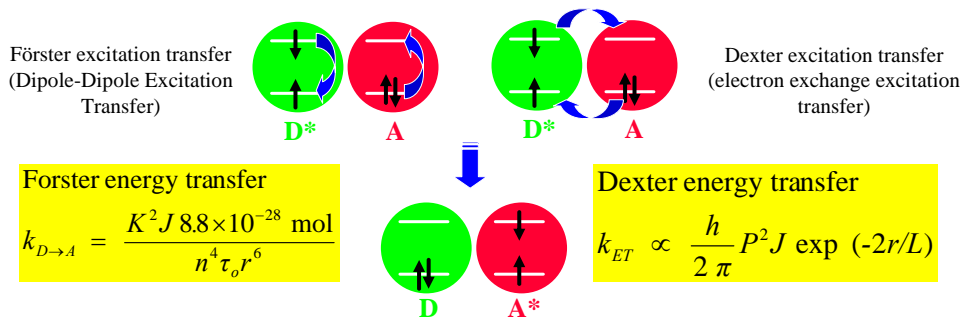


Förster: overlap of spectra, dipole interaction
Dexter: overlap of wavefunctions



Energy Transfer Processes

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Overlap integral : $J = \int \frac{\epsilon_A(\tilde{\nu}) \cdot F_D(\tilde{\nu})}{\tilde{\nu}^4} d\tilde{\nu}$

$$W_{DA} = k_r^D \left(\frac{R_0}{R} \right)^6 R_0^6 = 8.8 \cdot 10^{17} \cdot \frac{\kappa^2}{n^4} \cdot \int \frac{\epsilon_A(\tilde{\nu}) \cdot F_D(\tilde{\nu})}{\tilde{\nu}^4} d\tilde{\nu}$$

For photosynthetic systems R is typically 1 nm, R_0 is typically 8 nm.

$$k_r^D \approx 5 \cdot 10^7 \text{ s}^{-1} \rightarrow W_{DA} \approx 10^{13} \text{ s}^{-1}$$



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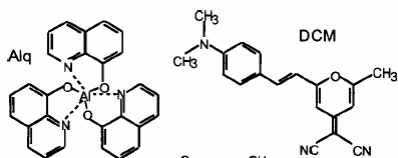
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Förster radius

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Excitation dynamics of dye doped tris(8-hydroxy quinoline) aluminum films

K. Read, H. S. Karlsson, M. M. Murnane and H. C. Kapteyn, R. Haight, J. Appl. Phys. 90, 294 (2001)



$$R_0^6 = \frac{0.5291 \kappa^2}{n^4 N_A} \cdot \int \frac{\epsilon_A(\tilde{\nu}) \cdot F_D(\tilde{\nu})}{\tilde{\nu}^4} d\tilde{\nu}$$

κ = donor/acceptor orientation factor;
 $\kappa^2 = 2/3$ for a randomly deposited film
 N_A is Avogadro's number
 $n = 1.7$ for Alq3
 $R_0 = 31 \text{ \AA}$

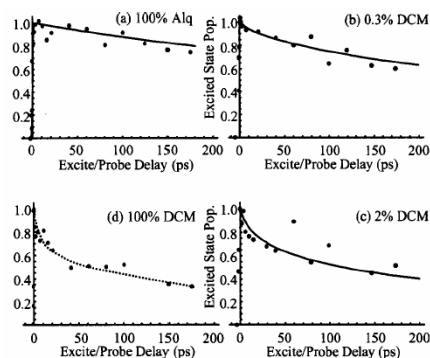
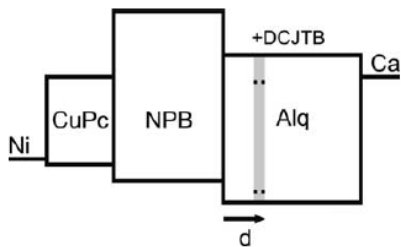


FIG. 3. Excited state population as a function of excite/probe delay for the sample compositions (a) 100% Alq, (b) Alq+0.3%DCM, (c) Alq+2%DCM, and (d) 100% DCM. The 100% DCM sample was excited with $68 \mu\text{J}/\text{cm}^2$, and all others were excited with $91 \mu\text{J}/\text{cm}^2$ (1.8×10^{27} phot/cm²) of 90 fs 3.14 eV laser pulses. The solid curve, (a) represents bimolecular singlet annihilation. The solid curves, (b) and (c), are from fits including excitation transfer, excimer formation, and stimulated emission. The dotted curve, (d), is only a guide to the eye.

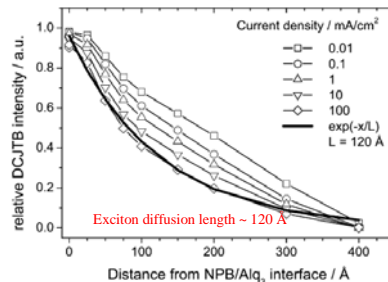
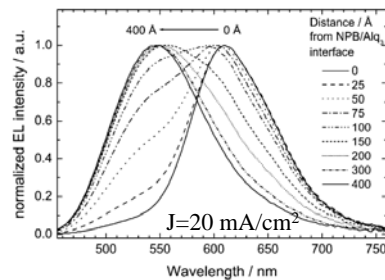


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Schematic energy level diagram of delta-doped devices having a 25 Å Alq₃/DCJTB (1%) sensing layer at various positions (d) in the Alq₃ layer. The device structure is Ni/CuPc (150 Å)/NPB (500 Å)/Alq₃ (500 Å)/Ca (200 Å).

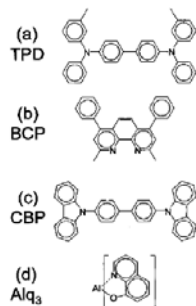


T.A. Beierlein, B. Ruhstaller, D.J. Gundlach, H. Riel, S. Karg, C. Rost, W. RieB, Synth. Met. 138, 213 (2003)

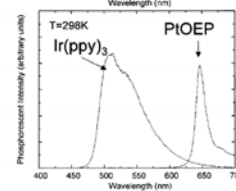
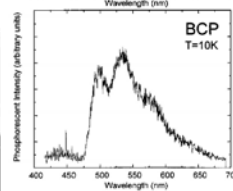
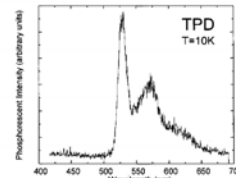
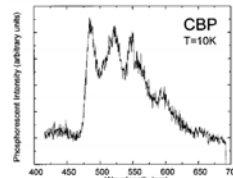
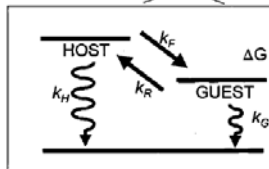
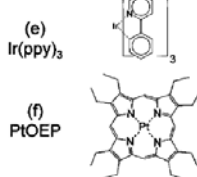


Triplet energy of R & G phosphors

HOSTS



GUESTS



Material	Triplet energy (±0.1 eV)	Triplet lifetime
PtOEP	1.9	110 ± 10 μs ^a
Ir(ppy) ₃	2.4	0.8 ± 0.1 μs ^b
CBP	2.6	> 1 s
BCP	2.5	< 10 μs
TPD	2.3	200 ± 50 μs
Alq ₃ ^c	2.0	25 ± 15 μs

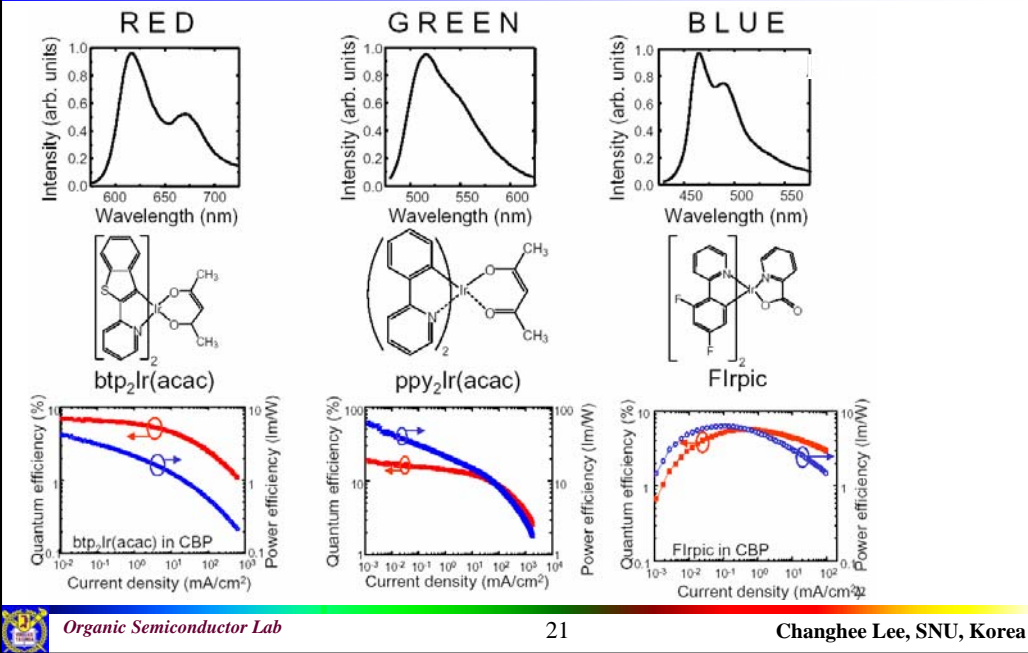
Guest (lifetime)	Host	ΔG (± 0.1 eV)	Host lifetime	Emission lifetime (μs)	Trapping on guest	EL quantum efficiency
PtOEP (110 ± 10 μs)	CBP	-0.7	> 1 s	80 ± 5	Yes	6%
Ir(ppy) ₃ (0.8 ± 0.1 μs)	Ir(ppy) ₃	-0.5	< 0.1 μs	80 ± 5	?	3%
	TPD	-0.4	200 ± 50 μs	80 ± 5	Yes	3%
	Alq ₃	-0.1	25 ± 15 μs	40 ± 5	No	3%
Ir(ppy) ₃ (0.8 ± 0.1 μs)	CBP	-0.2	> 1 s	0.4 ± 0.05	Yes	8%
	TPD	+0.1	200 ± 50 μs	15 ± 2	No	3%
	Alq ₃	+0.4	25 ± 15 μs	< 0.1	?	< 0.1%

M. A. Baldo and S. R. Forrest, Phys. Rev. B 62, 10958–10966 (2000).



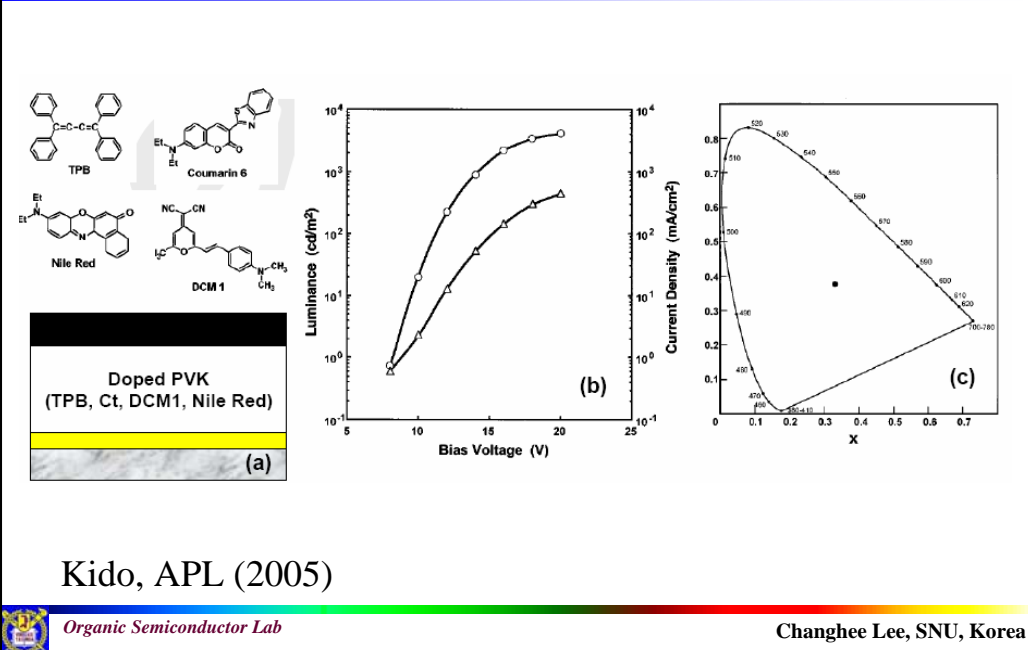
Organic Electrophosphorescence devices

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Single emitting layer

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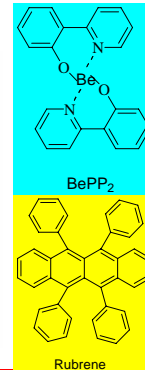
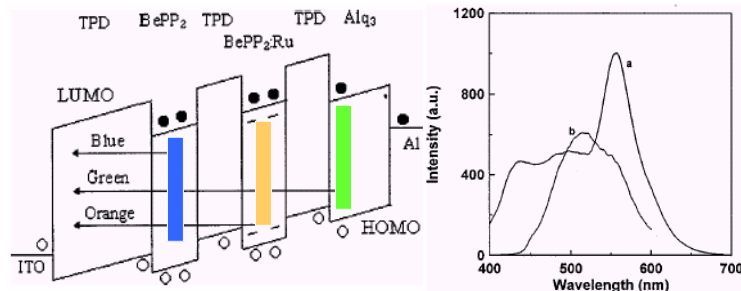


Multi-Quantum Well Structure

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1. The confinement of charge carriers in light-emitting quantum wells can enhance the forming probability of excitons and the light-emitting efficiencies of the devices.
2. Compared with multi-layer white OLEDs, the influence of band gap matching can be negligible, and the positions of different color light-emitting quantum wells can be exchangeable.
3. Easy turning of Commission International de l'Eclairage (CIE) chromaticity

0.41 lm/W, (0.32, 0.38) at 9V



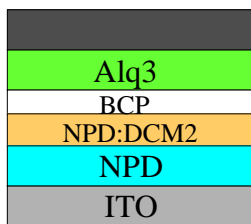
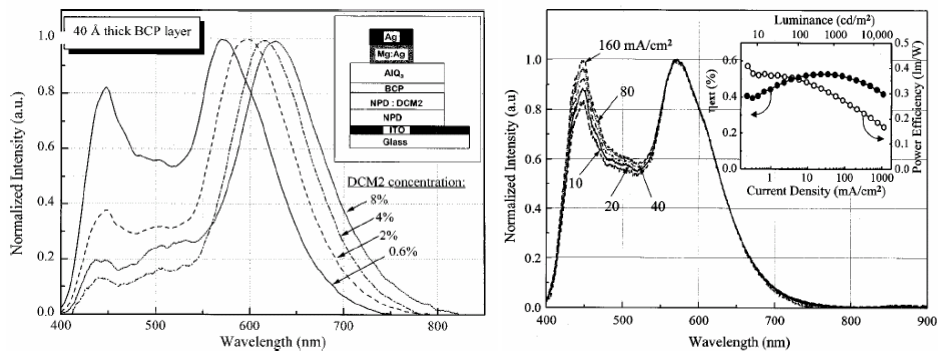
Z. Y. Xie (Jilin U), *Appl. Phys. Lett.*, **74**, 1999, 641

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Complementary Color Stack

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Interlayer sequential energy transfer (ISET):

NPD → Alq3 → DCM2

Hole-blocking layer

0.35 lm/W, (0.33, 0.33), and 100 cd/m² at 11.5 V

R. S. Deshpande (Princeton U.), *Appl. Phys. Lett.*, **75**, 1999, 888

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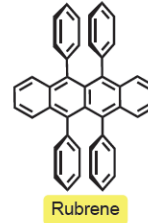
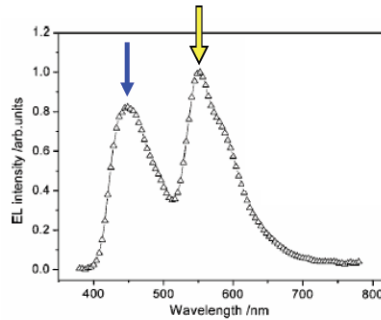
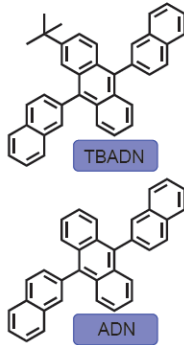
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Complementary Color Stack

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0.025% Rubrene/ 2.5% TBADN/ ADN

Device	EML	LO (cd/m ²)	QE
1	0.02% Rubrene/ ADN	17,280	1.08%
2	0.025% Rubrene/ 2.5% TBADN/ ADN	20,100	2.41%



TBADN = 9,10-di-(2-naphthyl)-2-t-butyl-anthracene

ADN = 9,10-di-(2-naphthyl)-anthracene

Rubrene = 5,6,11,12-tetraphenylanthracene

L. Wang et al., *J. Appl. Phys.* **2005**, 97, 114503.

44



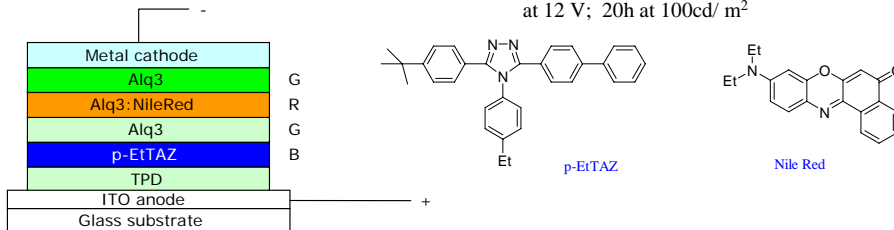
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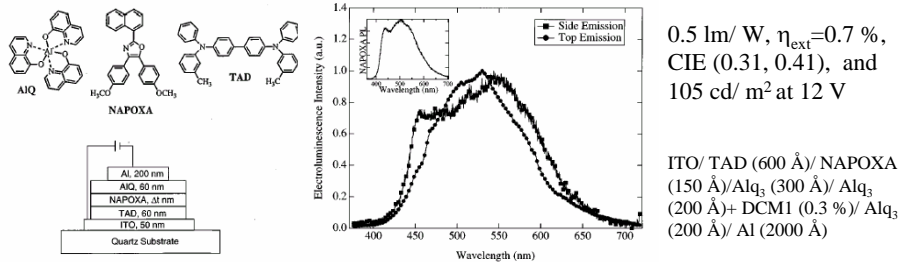
Multilayer RGB Stacks

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J. Kido (Yamagata U), *Science*, **267**, 1995, 1332. 0.5 lm/W, ~ 300cd/ m², and (0.335, 0.415) at 12 V; 20h at 100cd/ m²



R. H. Jordan (AT&T), *Appl. Phys. Lett.*, **68**, 1996, 1192.



0.5 lm/ W, $\eta_{ext}=0.7\%$,
CIE (0.31, 0.41), and
105 cd/ m² at 12 V

ITO/ TAD (600 Å)/ NAPOXA
(150 Å)/Alq₃ (300 Å)/ Alq₃
(200 Å)+ DCM1 (0.3 %)/ Alq₃
(200 Å)/ Al (2000 Å)

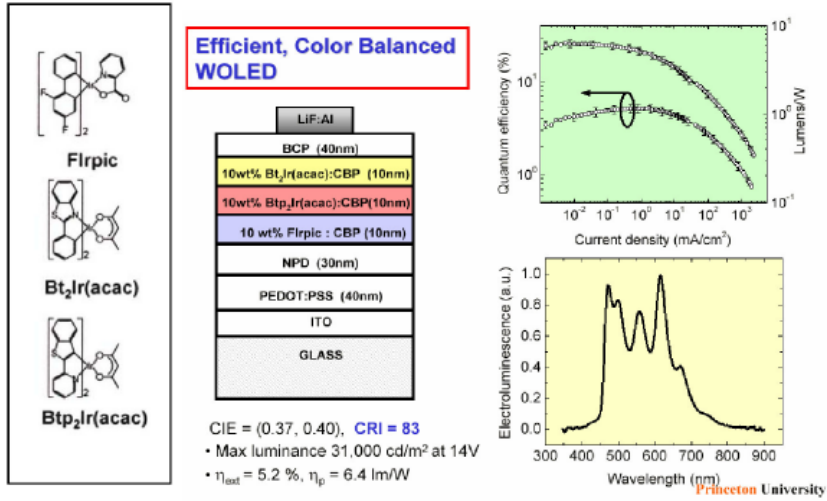


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RGB white OLEDs: Phosphorescence

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S. R. Forrest et al., Adv. Mater. **14**, 1035 (2002)



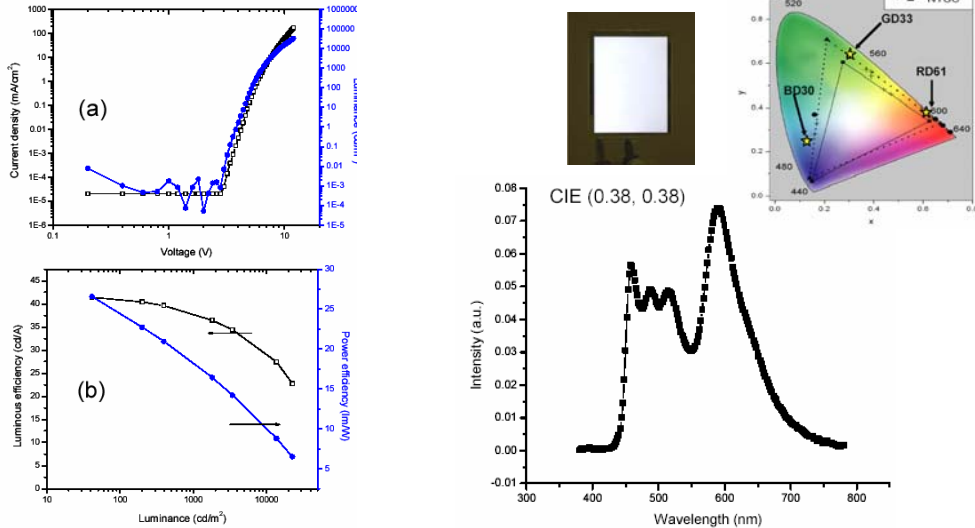
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White Phosphorescent OLEDs

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Yeh-Jiun Tung et al. (Universal Display Corporation), SID 04 Digest 48



38 cd/A, 18.4 lm/W and 16% EQE with CIE of (0.39, 0.39) at 1000 cd/m²

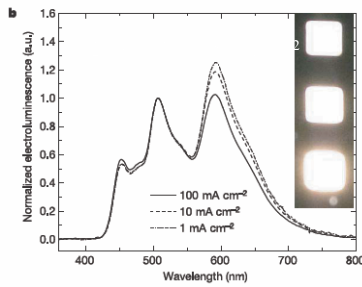
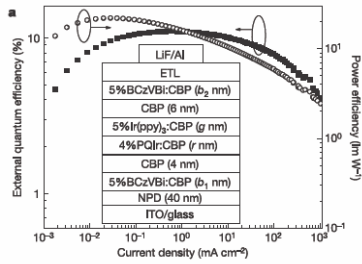


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High efficiency white OLEDs

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General Electric
15 lm/W (2 ft. x 2 ft.) @ 1200 lumen

Y. Sun, N. C. Giebink, H. Kanno, B. Ma, M. E. Thompson, S. R. Forrest, Nature **440**, 908 (2006)

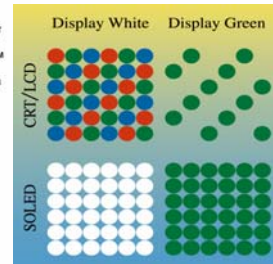
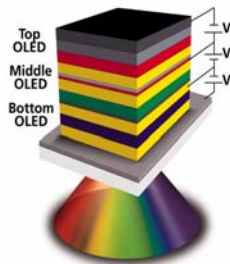
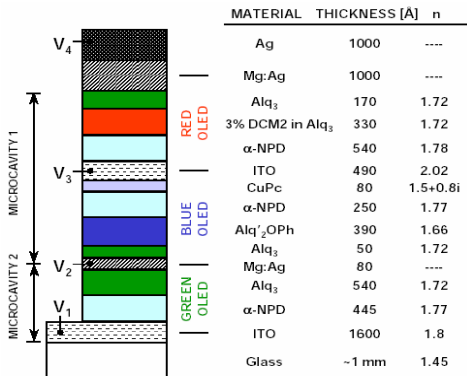


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Full-Color Method – Stacked OLED

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High resolution but very difficult process (fabrication of electrodes)



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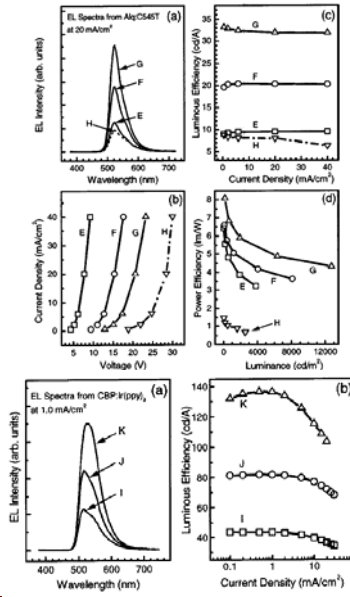
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High-efficiency tandem OLED

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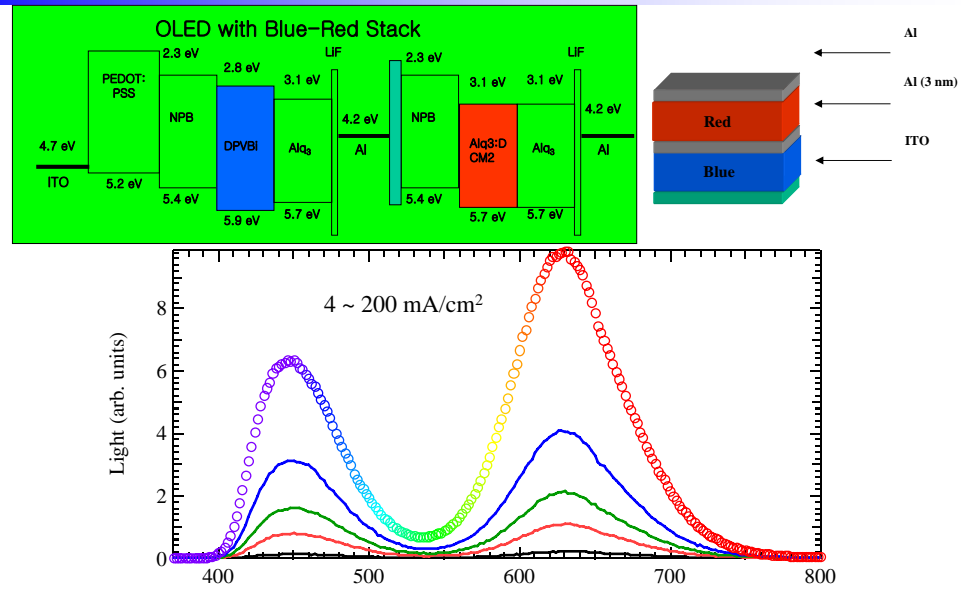
TABLE I. Layer structures of the OLED devices

Device or unit	Layer structure
Device A	ITO/SA1/ <u>EL-G</u> /OC1/ <u>EL-R</u> /SC1/Mg:Ag
Device B	ITO/SA1/ <u>EL-G</u> / <u>EL-R</u> /SC1/Mg:Ag
Device C	ITO/SA1/ <u>EL-G</u> /SC1/Mg:Ag
Device D	ITO/SA1/ <u>EL-R</u> /SC1/Mg:Ag
SA1	NPB (50 nm)
EL-G	NPB (25 nm)/Alq (20 nm)/Alq (5 nm)
OC1	Alq:Li (25 nm)/NPB:FeCl ₃ (60 nm)
EL-R	NPB (25 nm)/Alq:DCJTb (20 nm)/Alq (5 nm)
SC1	Alq (35 nm)
Device E	ITO/SA2/ <u>EL2</u> /SC2/Mg:Ag
Device F	ITO/SA2/ <u>EL2</u> /OC2/ <u>EL2</u> /SC2/Mg:Ag
Device G	ITO/SA2/ <u>EL2</u> /OC2/ <u>EL2</u> /OC2/ <u>EL2</u> /SC2/Mg:Ag
Device H	ITO/SA2/ <u>EL2</u> / <u>EL2</u> / <u>EL2</u> /SC2/Mg:Ag
SA2	NPB (60 nm)
EL2	NPB (30 nm)/Alq:C545T (20 nm)/Alq (10 nm)
OC2	Alq:Li (30 nm)/NPB:FeCl ₃ (60 nm)
SC2	Alq (30 nm)
Device I	ITO/SA3/ <u>EL3</u> /SC3/Mg:Ag
Device J	ITO/SA3/ <u>EL3</u> /OC3/ <u>EL3</u> /SC3/Mg:Ag
Device K	ITO/SA3/ <u>EL3</u> /OC3/ <u>EL3</u> /OC3/ <u>EL3</u> /SC3/Mg:Ag
SA3	NPB (60 nm)
EL3	NPB (30 nm)/CBP: Ir(pppy) ₃ (20 nm)/TPBI (20 nm)
OC3	Alq:Li (24 nm)/NPB:FeCl ₃ (48 nm)
SC3	TPBI (40 nm)



White OLEDs with multilayer stack structure

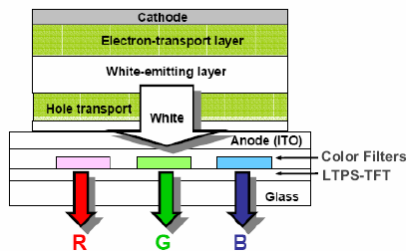
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Methods of Color Patterning (White OLED + RGB Color Filters)

(Prototype (2002) Kodak/Sanyo
15" AMOLED W-RGB

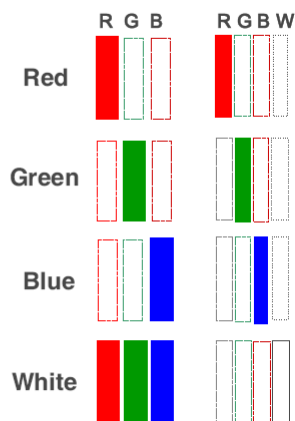
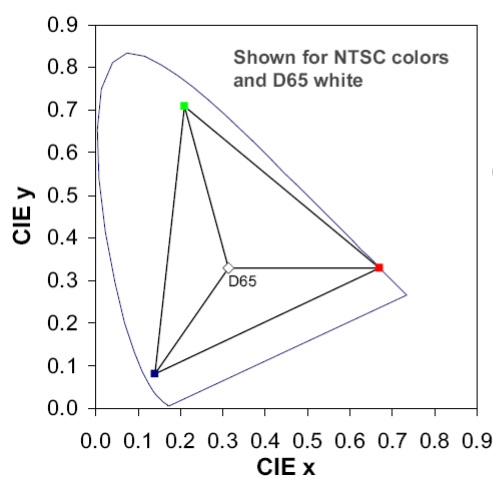
Kodak commenced R&D on white OLED materials, device, and display design several years ago.



Contents	Specifications
Display size	14.7 inch
Aspect ratio	16:9
Dot Counts	1280 × RGB × 720
Dot pitch	85 × 255
Color type	RGB stripe
Contrast	>500
Thickness	1.4 mm

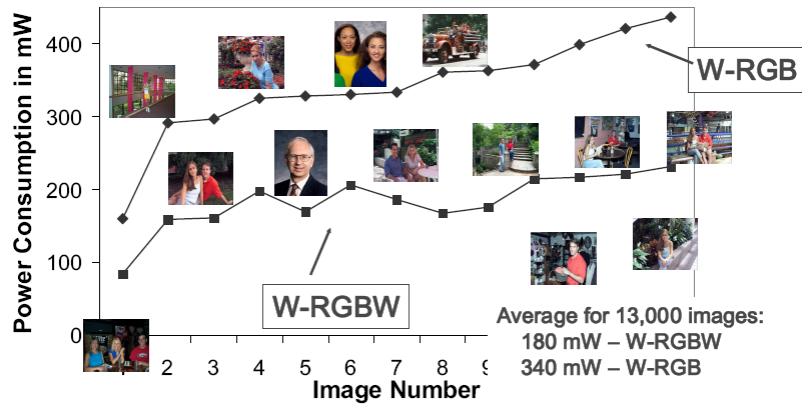


W-RGB and W-RGBW – Primary Colors

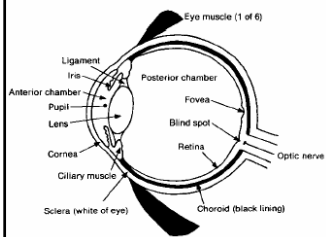


W-RGB and W-RGBW Power Consumption

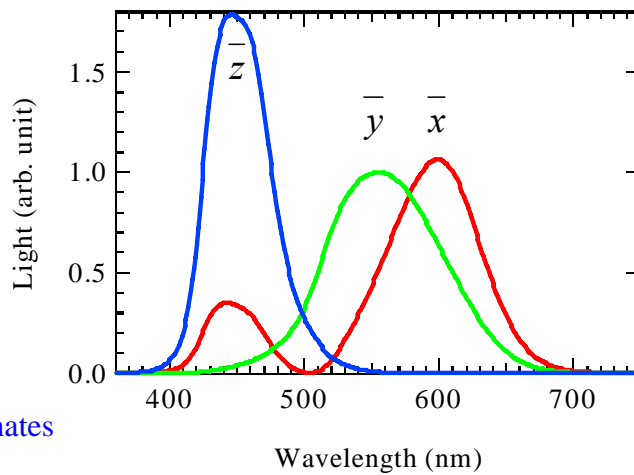
2.2" diagonal, 100cd/m² white after 44% T circular polarizer



CIE 1931 Color Matching Functions



CIE 1931 Color Matching Functions (2 deg. Observer)

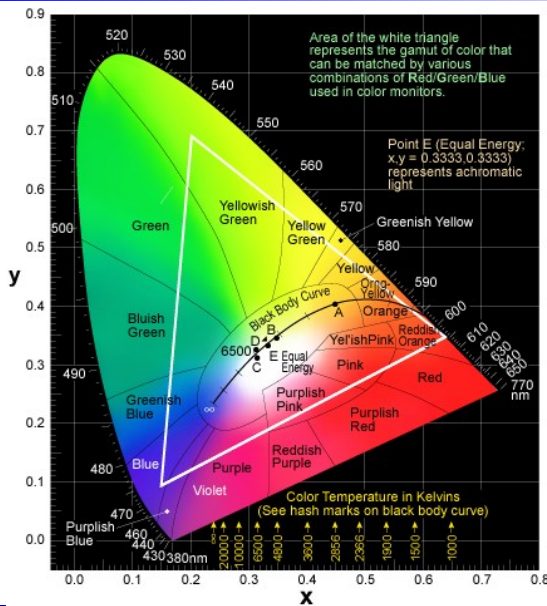


- Chromaticity coordinates
- Color temperature
- Color rendering index (CRI)



Chromaticity Coordinates & Color Temperature

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$$X = K \int_{380}^{780} S(\lambda) \bar{x} d\lambda \quad K = 683 \text{ lm/W}$$

$$Y = K \int_{380}^{780} S(\lambda) \bar{y} d\lambda$$

$$Z = K \int_{380}^{780} S(\lambda) \bar{z} d\lambda$$

$$x = \frac{X}{X+Y+Z} \quad y = \frac{Y}{X+Y+Z}$$

$$x + y + z = 1$$

- A black body radiator (Planckian Source) glows with a color that is solely dependent on its temperature (in K).

- Standard source

D₆₅ (daylight, 6500 K)

(x,y) = (0.312, 0.329)

E = Equal Energy point: (0.333, 0.333)

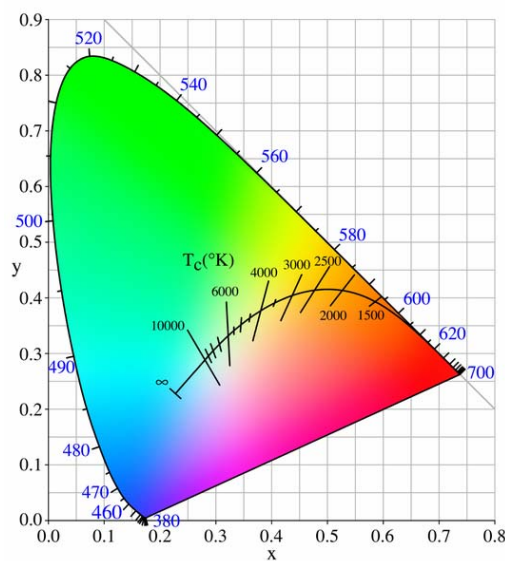


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Correlated color temperature

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Correlated colour temperature (CCT)

= Temperature of a Planckian radiator having the chromaticity nearest the chromaticity associated with the given spectral distribution on a CIE 1931 chromaticity diagram.

- Only applicable for sources close to the black body curve (white light).

- Standard source:

D₆₅ (daylight, 6500 K) (x,y) = (0.312, 0.329)

E = Equal Energy point: (0.333, 0.333)

McCamy's approximate formula

$$T_{CCT} = 437n^3 + 3601n^2 + 6861n + 5517$$

where $n = (x - 0.3320) / (0.1858 - y)$, and x, y are the CIE 1931 chromaticity coordinates.

Ref. McCamy, Color Res. Appl. **18**, 150 (1993).



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Color Rendering Index (CRI)

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- **Color Rendering Index (CRI):** a numerical system that rates the "color rendering" ability of the light source in comparison with natural daylight (CRI=100, the highest possible CRI).
- CRI is a relative measure of the colorimetric shift of an object when lit by a particular light source, compared with how the object would appear under a reference light source of similar color temperature.

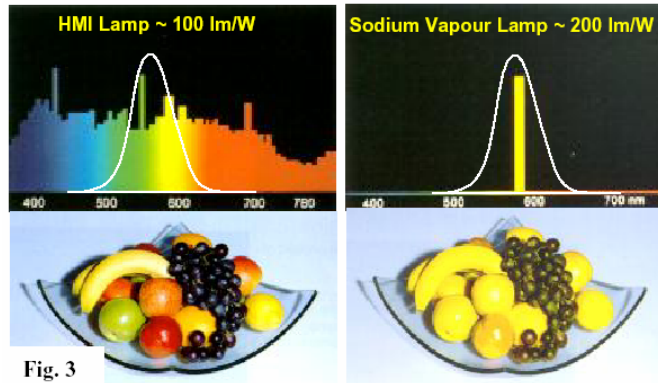


Fig. 3



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Calculation Method of CRI

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1. Select a reference illuminant (Planck blackbody radiation below 6000K)

$$S_r(\lambda) \xrightarrow{\bar{x}, \bar{y}, \bar{z}} x_r(\lambda), y_r(\lambda)$$

$$X = K \int_{380}^{780} S(\lambda) \bar{x} d\lambda \quad Y = K \int_{380}^{780} S(\lambda) \bar{y} d\lambda$$

$$Z = K \int_{380}^{780} S(\lambda) \bar{z} d\lambda$$

$$x = \frac{X}{X+Y+Z}, \quad y = \frac{Y}{X+Y+Z}$$

2. Measure the spectrum of the test source.

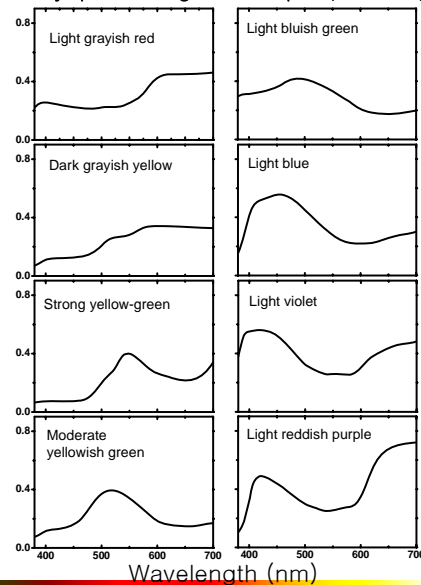
$$S_k(\lambda) \xrightarrow{\bar{x}, \bar{y}, \bar{z}} x_k(\lambda), y_k(\lambda)$$

3. Determine the reflected spectra from each of the eight test samples

$$S_r(\lambda) \rho(\lambda)_i \rightarrow (x_{ri}, y_{ri})$$

$$S_k(\lambda) \rho(\lambda)_i \rightarrow (x_{ki}, y_{ki})$$

Reflectivity spectra of eight test samples (CIE 1964)



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Calculation Method of CRI

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4. Transform the colorimetric data from the CIE 1931 values (X, Y, Z, x, y) to the (u, v) coordinates of the CIE 1960 *uniform chromaticity scale* (UCS) diagram by means of the following:

$$u = \frac{4X}{X + 15Y + 3Z} = \frac{4x}{-2x + 12y + 3}$$

$$v = \frac{6Y}{X + 15Y + 3Z} = \frac{6y}{-2x + 12y + 3}$$

5. To account for the adaptive color shift due to the different state of chromatic adaptation under the lamp to be tested and under the reference illuminant use the following formula:

$$u'_{ki} = \frac{10.872 + 0.404c_r c_{ki} / c_k - 4d_r d_{ki} / d_k}{16.518 + 1.481c_r c_{ki} / c_k - d_r d_{ki} / d_k}$$

$$v'_{ki} = \frac{5.520}{16.518 + 1.481c_r c_{ki} / c_k - d_r d_{ki} / d_k}$$

$$c = (4 - u - 10v) / v, \quad d = (1.708v + 0.404 - 1.481u) / v$$



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Calculation Method of CRI

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5. Calculate lightness indices for all reflected spectra:

$$W = 24Y^{1/3} - 17$$

6. Calculate the special color rendering indices for each test-color sample.

$$R_i = 100 - 4.6 \{ [W_{ki} - W_{ri}]^2 + 13^2 [W_{ki}(u'_{ki} - u_r) - W_{ri}(u_{ri} - u_r)]^2 + 13^2 [W_{ki}(v'_{ki} - v_r) - W_{ri}(v_{ri} - v_r)]^2 \}^{1/2}$$

7. Calculate the general color rendering index.

$$CRI \text{ value: } R_a = \frac{1}{8} \sum_{i=1}^8 R_i$$



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